



CEDM7001

SURFACE MOUNT  
N-CHANNEL  
ENHANCEMENT-MODE  
SILICON MOSFET

**TLP**<sup>TM</sup>  
*Tiny Leadless Package*



Top View



Bottom View

SOT-883L CASE

MARKING CODE: CEDM7001: H

**Central**<sup>TM</sup>  
Semiconductor Corp.

**DESCRIPTION:**

The CENTRAL SEMICONDUCTOR CEDM7001 is an Enhancement-mode N-Channel Field Effect Transistor, manufactured by the N-Channel DMOS Process, designed for high speed pulsed amplifier and driver applications. This MOSFET offers Low  $r_{DS(on)}$  and Low Threshold Voltage.

**FEATURES:**

- Power Dissipation 100mW
- Low Package Profile, 0.4mm
- Low  $r_{DS(on)}$
- Low Threshold Voltage
- Logic Level Compatible
- Small, TLP<sup>TM</sup> 1x0.6mm, SOT-883L Leadless Surface Mount Package

**APPLICATIONS:**

- Load/Power Switches
- Power Supply Converter Circuits
- Battery Powered Portable Equipment

**MAXIMUM RATINGS (T<sub>A</sub>=25°C)**

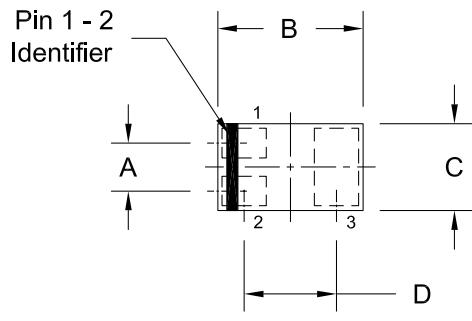
	SYMBOL	UNITS
Drain-Source Voltage	V <sub>DS</sub>	V
Gate-Source Voltage	V <sub>GS</sub>	V
Continuous Drain Current (Steady State)	I <sub>D</sub>	mA
Continuous Drain Current	I <sub>D</sub>	mA
Power Dissipation	P <sub>D</sub>	mW
Operating and Storage Junction Temperature	T <sub>J</sub> , T <sub>stg</sub>	°C

**ELECTRICAL CHARACTERISTICS (T<sub>A</sub>=25°C unless otherwise noted)**

SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
I <sub>GSSF</sub>	V <sub>GS</sub> =10V, V <sub>DS</sub> =0V			1.0	µA
I <sub>GSSR</sub>	V <sub>GS</sub> =10V, V <sub>DS</sub> =0V			1.0	µA
I <sub>DSS</sub>	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V			1.0	µA
BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =100µA	20			V
V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250µA	0.6		0.9	V
r <sub>DS(ON)</sub>	V <sub>GS</sub> =4.0V, I <sub>D</sub> =10mA			3.0	Ω
r <sub>DS(ON)</sub>	V <sub>GS</sub> =2.5V, I <sub>D</sub> =10mA			4.0	Ω
r <sub>DS(ON)</sub>	V <sub>GS</sub> =1.5V, I <sub>D</sub> =1.0mA			15	Ω
Y <sub>fs</sub>	V <sub>DS</sub> =10V, I <sub>D</sub> =100mA	100			mS
C <sub>rss</sub>	V <sub>DS</sub> =3.0V, V <sub>GS</sub> =0, f=1.0MHz		4.0		pF
C <sub>iss</sub>	V <sub>DS</sub> =3.0V, V <sub>GS</sub> =0, f=1.0MHz		9.0		pF
C <sub>oss</sub>	V <sub>DS</sub> =3.0V, V <sub>GS</sub> =0, f=1.0MHz		9.5		pF
t <sub>on</sub>	V <sub>DD</sub> =3.0V, V <sub>GS</sub> =2.5V, I <sub>D</sub> =10mA		50		ns
t <sub>off</sub>	V <sub>DD</sub> =3.0V, V <sub>GS</sub> =2.5V, I <sub>D</sub> =10mA		75		ns

R3 (31-July 2007)

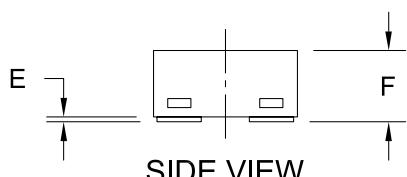
SOT-883L - MECHANICAL OUTLINE



TOP VIEW

SYMBOL	DIMENSIONS			
	INCHES	MILLIMETERS	MIN	MAX
A	0.014	0.35		
B	0.037	0.95	0.041	1.05
C	0.022	0.55	0.026	0.65
D	0.026	0.65		
E	0.000	0.002	0.00	0.05
F	0.012	0.30	0.016	0.40
G	0.005	0.13	0.007	0.18
H	0.008	0.20	0.012	0.30
J	0.018	0.45	0.022	0.55
K	0.008	0.20	0.012	0.30

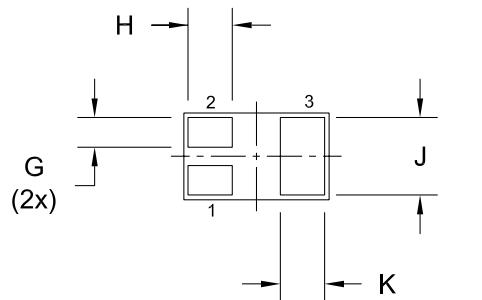
SOT-883L (REV:R2)



SIDE VIEW

LEAD CODE:

- 1) GATE
- 2) SOURCE
- 3) DRAIN



BOTTOM VIEW R2

R3 (31-July 2007)